2SK1697

Silicon N-Channel MOS FET

HITACHI

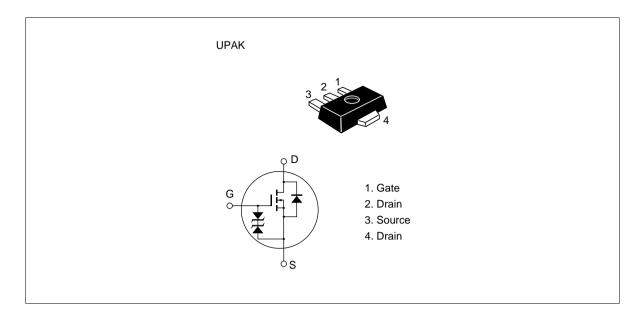
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- 4 V gate drive device --- can be driven from 5 V source.
- Suitable for DC DC converter, motor drive, power switch, solenoid drive

Outline





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Absolute Maximum Ratings $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit	
Drain to source voltage	V _{DSS}	60	V	
Gate to source voltage	V_{GSS}	±20	V	
Drain current	I _D	0.5	Α	
Drain peak current	l _{D(pulse)} *1	1.5	А	
Body to drain diode reverse drain current	I _{DR}	0.5	Α	
Channel dissipation	Pch*2	1	W	
Channel temperature	Tch	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

Notes 1. PW \leq 10 μ s, duty cycle \leq 1%

- 2. When using the alumina ceramic board (12.5 \times 20 \times 0.7 mm)
- 3. Marking is "EY".

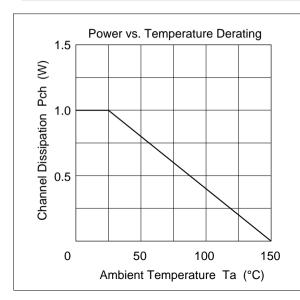
Electrical Characteristics ($Ta = 25^{\circ}C$)

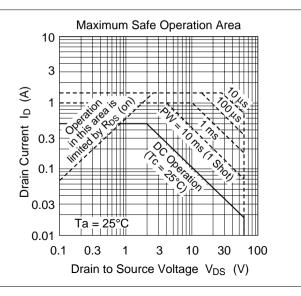
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	60	_	_	V	$I_{D} = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	_	_	V	$I_{G} = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I _{DSS}	_	_	50	μΑ	$V_{DS} = 50 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	_	2.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	R _{DS(on)}	_	1.3	1.7	Ω	$I_D = 0.3 \text{ A}, V_{GS} = 10 \text{ V}^{*1}$
		_	1.8	2.5	Ω	$I_D = 0.3 \text{ A}, V_{GS} = 4 \text{ V}^{*1}$
Forward transfer admittance	y _{fs}	0.25	0.38	_	S	$I_D = 0.3 \text{ A}, V_{DS} = 10 \text{ V}^{*1}$
Input capacitance	Ciss	_	30	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$
Output capacitance	Coss	_	13	_	pF	f = 1 MHz
Reverse transfer capacitance	Crss	_	4	_	pF	<u> </u>
Turn-on delay time	t _{d(on)}	_	3	_	ns	$I_D = 0.3 \text{ A}, V_{GS} = 10 \text{ V},$
Rise time	t _r	_	8	_	ns	$R_L = 100 \Omega$
Turn-off delay time	t _{d(off)}	_	18	_	ns	<u> </u>
Fall time	t _f	_	14	_	ns	_
Body to drain diode forward voltage	V_{DF}	_	1	_	V	$I_F = 0.5 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery time	t _{rr}		45		ns	$I_F = 0.5 \text{ A}, V_{GS} = 0,$ $di_F/dt = 50 \text{ A}/\mu\text{s}$

Note 1. Pulse test

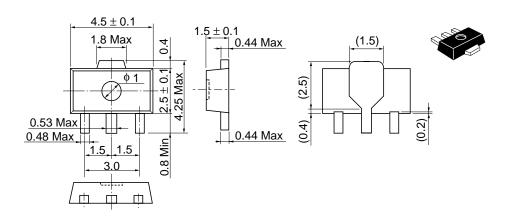
See characteristic curve of 2SK1336.

2SK1697





Unit: mm



Hitachi Code	UPAK
JEDEC	_
EIAJ	Conforms
Weight (reference value)	0.050 g

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